Ordering number:ENN2557B

NPN Epitaxial Planar Silicon Transistor

2SC4188

Ultrahigh-Definition CRT Display Video Output Applications

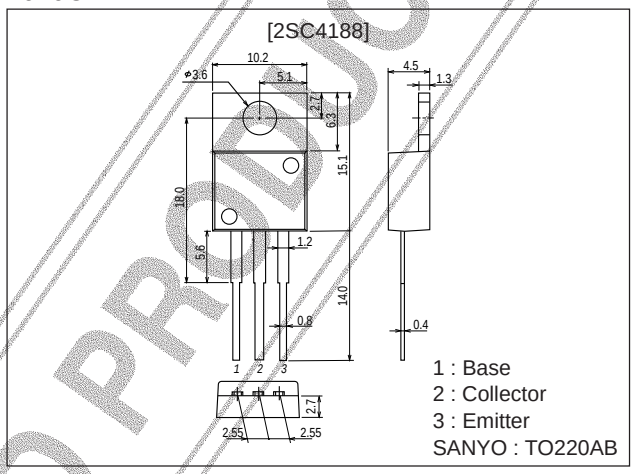
Features

- High breakdown voltage : V_{CEO}≥200V.
- Small reverse transfer capacitance and excellent high frequency characteristic : C_{re}=1.3pF typ.
- Adoption of FBET process.

Package Dimensions

unit:mm

2010C



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		200	V
Collecor-to-Emitter Voltage	V_{CEO}		200	V
Emitter-to-Base Voltage	V_{EBO}		5	V
Collector Current	I_C		100	mA
Collector Current (Pulse)	I_{CP}		200	mA
Collector Dissipation	P_C		1.5	W
		Tc=25˚C	10	W
Junction Tempreature	Tj		150	˚C
Storage temperature	Tstg		–55 to +150	˚C

The 2SC4188 is classified by 10mA h_{FE} as follows :

Rank	C	D	E	F
h_{FE}	40 to 80	60 to 120	100 to 200	160 to 320

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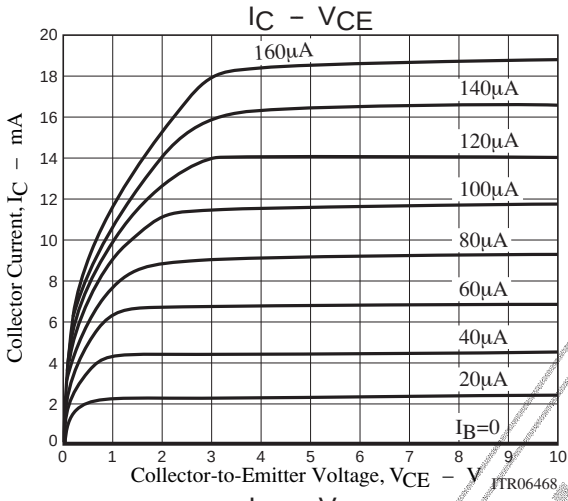
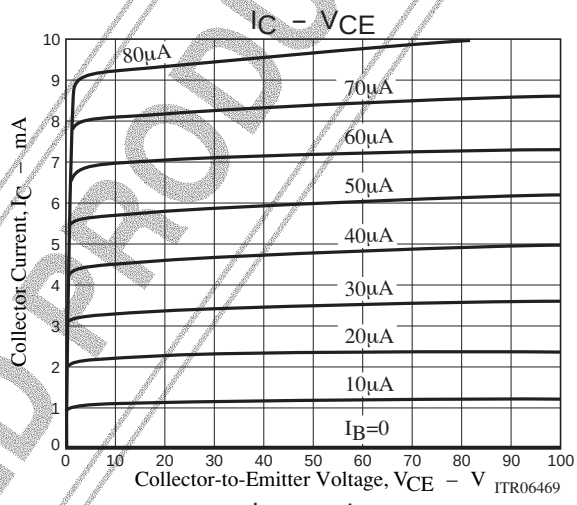
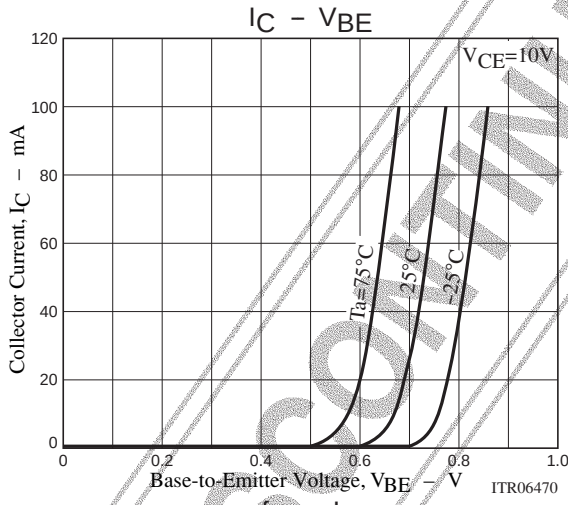
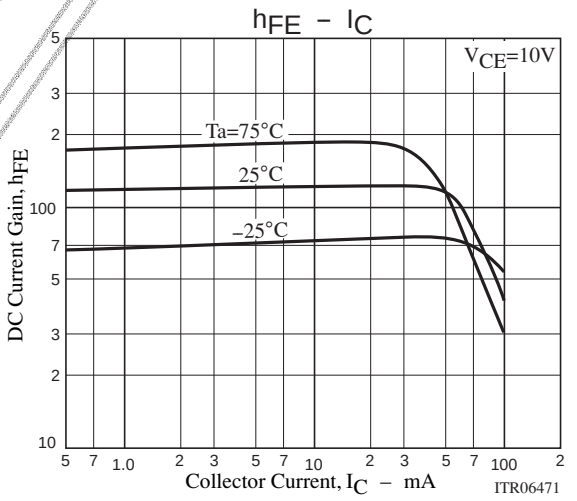
Electrical Characteristics at Ta = 25°C

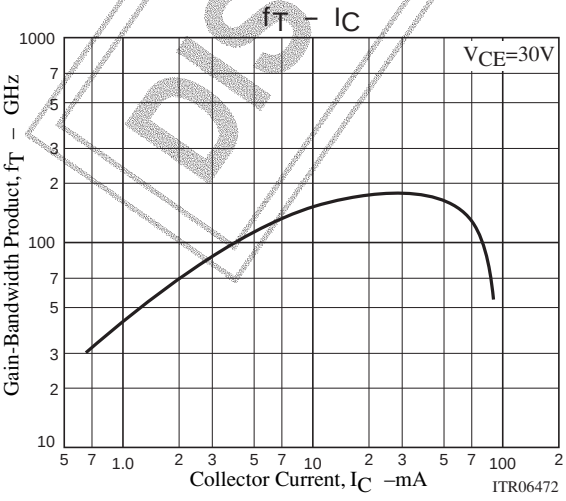
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=150V, I_E=0			0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=10V, I_C=10mA	40*		320*	
Gain-Bandwidth Product	f_T	V_{CE}=30V, I_C=10mA		150		MHz
Output Capacitance	C_{ob}	V_{CB}=30V, f=1MHz		1.8		pF
Reverse Transfer Capacitance	C_{re}	V_{CB}=30V, f=1MHz		1.3		pF
Collector-to-Emitter Saturatin Voltage	$V_{CE(sat)}$	I_C=20mA, I_B=2mA			0.6	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=20mA, I_B=2mA			1.0	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=10μA, I_E=0	200			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	200			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	5			V

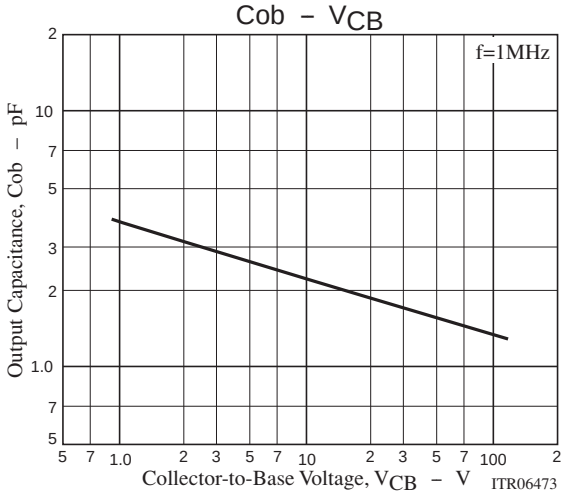




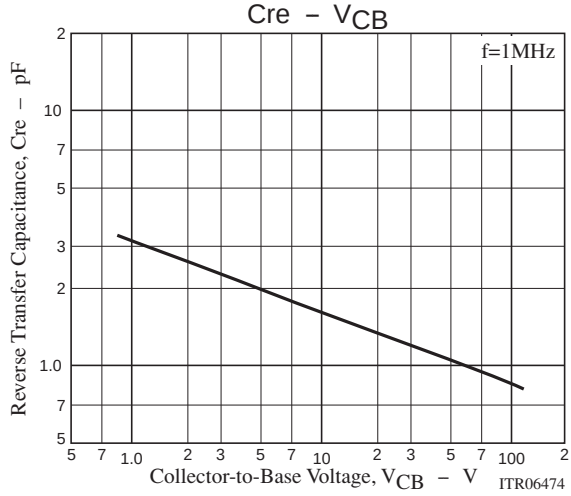




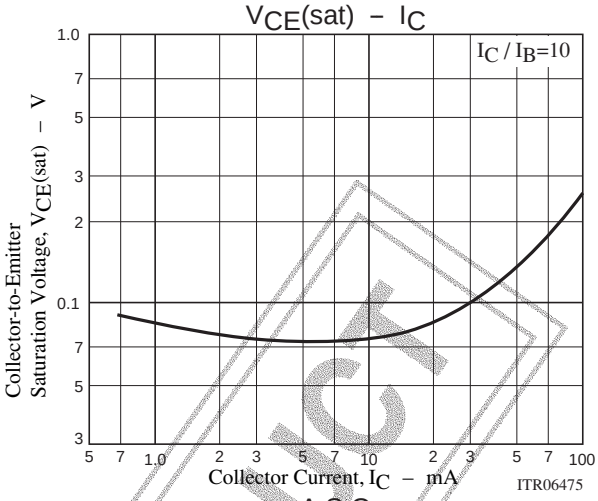




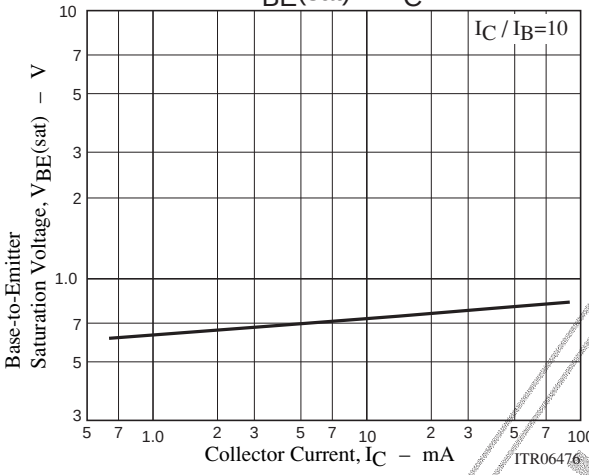
Cre – V_{CB}



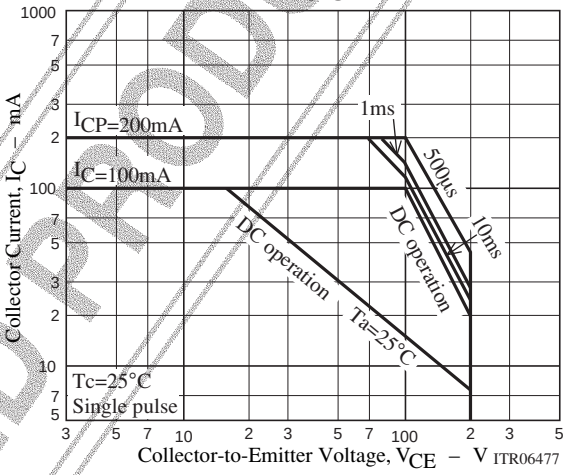
V_{CE}(sat) – I_C



V_{BE}(sat) – I_C



ASO



P_C – Ta